

Description

The XPX20150RD uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a

Battery protection or in other Switching application.

Application

Battery protection

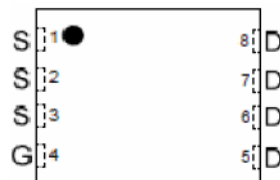
Load switch

Uninterruptible power supply

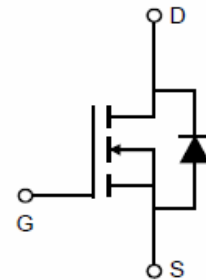
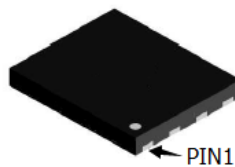
$$V_{DS} = 20V, I_D = 150A$$

$$R_{DS(ON)} = 1.6 \text{ m}\Omega @ V_{GS} = 10V$$

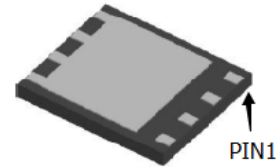
$$R_{DS(ON)} = 1.9 \text{ m}\Omega @ V_{GS} = 4.5V$$



Top View



Bottom View



Package Marking and Ordering Information

| Product ID | Pack | Marking | Qty(PCS) |
|------------|------------|---------|----------|
| XPX20150RD | PDFN5*6-8L | 20150 | 5000 |

Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$ unless otherwise noted)

| Symbol | Parameter | Rating | Units |
|---------------------------------|--|------------|--------------------|
| V_{DS} | Drain-Source Voltage | 20 | V |
| V_{GS} | Gate-Source Voltage | ± 12 | V |
| $I_D @ T_C = 25^\circ\text{C}$ | Continuous Drain Current ¹ | 150 | A |
| $I_D @ T_C = 100^\circ\text{C}$ | Continuous Drain Current ¹ | 65 | A |
| IDM | Pulsed Drain Current ² | 270 | A |
| EAS | Single Pulse Avalanche Energy ³ | 80 | mJ |
| IAS | Avalanche Current | 40 | A |
| $P_D @ T_C = 25^\circ\text{C}$ | Total Power Dissipation ⁴ | 83 | W |
| TSTG | Storage Temperature Range | -55 to 150 | $^\circ\text{C}$ |
| T_J | Operating Junction Temperature Range | -55 to 150 | $^\circ\text{C}$ |
| $R_{\theta JA}$ | Thermal Resistance Junction-ambient ¹ ($t \leq 10\text{S}$) | 20 | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance Junction-ambient ¹ (Steady State) | 55 | $^\circ\text{C/W}$ |
| $R_{\theta JC}$ | Thermal Resistance Junction-case ¹ | 1.5 | $^\circ\text{C/W}$ |

Electrical Characteristics (T_c=25°C unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-----------------|--|---|-----|------|-----|------|
| BVDSS | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =250uA | 20 | 23 | --- | V |
| VGS(th) | Gate Threshold Voltage | V _{GS} =V _{DS} , I _D =250uA | 0.5 | 0.68 | 1.0 | V |
| RDS(ON) | Static Drain-Source On-Resistance ² | V _{GS} =10V, I _D =20A | --- | 1.6 | 2.0 | mΩ |
| RDS(ON) | Static Drain-Source On-Resistance ² | V _{GS} =4.5V, I _D =20A | --- | 1.9 | 2.5 | mΩ |
| RDS(ON) | Static Drain-Source On-Resistance ² | V _{GS} =2.5V, I _D =20A | --- | 2.8 | 3.8 | mΩ |
| IDSS | Drain-Source Leakage Current | V _{DS} =16V, V _{GS} =0V, T _J =25°C | --- | --- | 1 | uA |
| | | V _{DS} =16V, V _{GS} =0V, T _J =125°C | --- | --- | 5 | |
| IGSS | Gate-Source Leakage Current | V _{GS} =±10V, V _{DS} =0V | --- | --- | ±10 | uA |
| Rg | Gate Resistance | V _{DS} =0V, V _{GS} =0V, f=1MHz | --- | 1.2 | --- | Ω |
| Qg | Total Gate Charge (10V) | V _{DS} =15V, V _{GS} =10V, I _D =20A | --- | 77 | --- | nC |
| Qgs | Gate-Source Charge | | --- | 8.7 | --- | |
| Qgd | Gate-Drain Charge | | --- | 14 | --- | |
| Td(on) | Turn-On Delay Time | V _{DD} =15V, V _{GS} =10V, R _G =3Ω, I _D =20A | --- | 10.2 | --- | ns |
| T _r | Rise Time | | --- | 11.7 | --- | |
| Td(off) | Turn-Off Delay Time | | --- | 56.4 | --- | |
| T _f | Fall Time | | --- | 16.2 | --- | |
| Ciss | Input Capacitance | V _{DS} =10V, V _{GS} =0V, f=1MHz | --- | 4307 | --- | pF |
| Coss | Output Capacitance | | --- | 501 | --- | |
| Crss | Reverse Transfer Capacitance | | --- | 321 | --- | |
| IS | Continuous Source Current ^{1,5} | V _G =V _D =0V, Force Current | --- | --- | 50 | A |
| VSD | Diode Forward Voltage ² | V _{GS} =0V, I _S =1A, T _J =25°C | --- | --- | 1.2 | V |
| trr | Reverse Recovery Time | IF=20A, di/dt=100A/μs, T _J =25°C | --- | 22 | --- | nS |
| Q _{rr} | Reverse Recovery Charge | | --- | 72 | --- | nC |

Note :

- 1、 The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、 The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3、 The EAS data shows Max. rating . The test condition is VDD=16V,VGS=10V,L=0.1mH,IAS=39A
- 4、 The power dissipation is limited by 175°C junction temperature
- 5、 The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|------------|----------------|-----------|------------|----------|
| XPX20150RD | XPX20150RD | DFN5X6-8L | - | - | 5000 |

Typical Characteristics

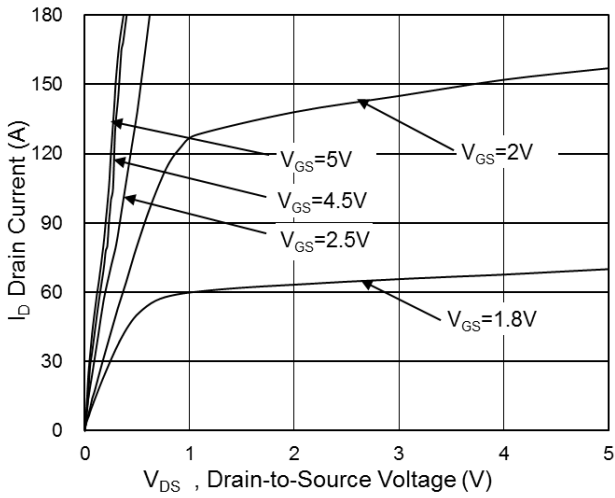


Fig.1 Typical Output Characteristics

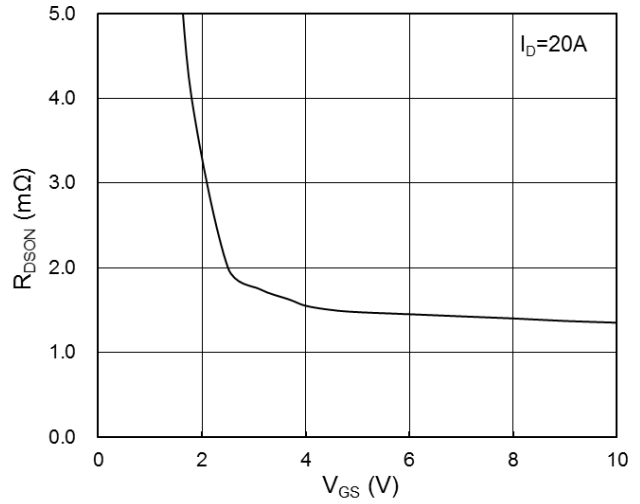


Fig.2 On-Resistance vs. Gate-Source Voltage

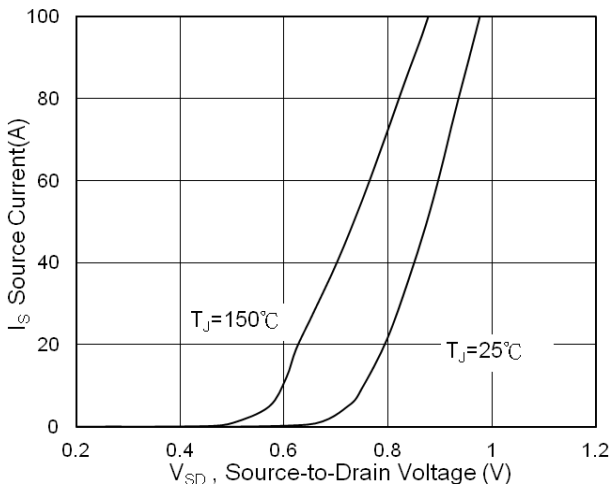


Fig.3 Forward Characteristics of Reverse

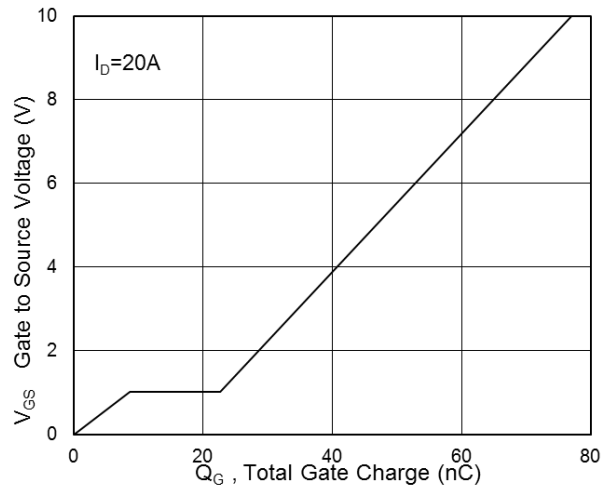


Fig.4 Gate-Charge Characteristics

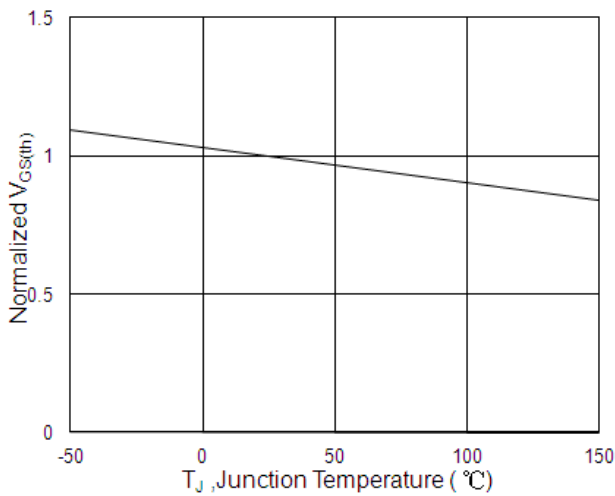


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

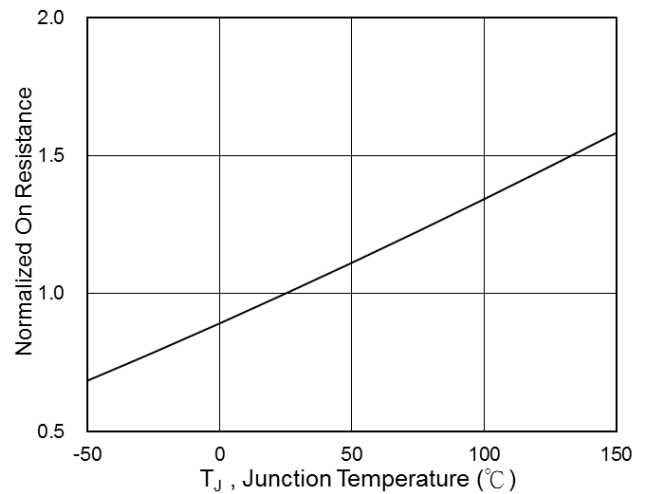


Fig.6 Normalized R_{DSON} vs. T_J

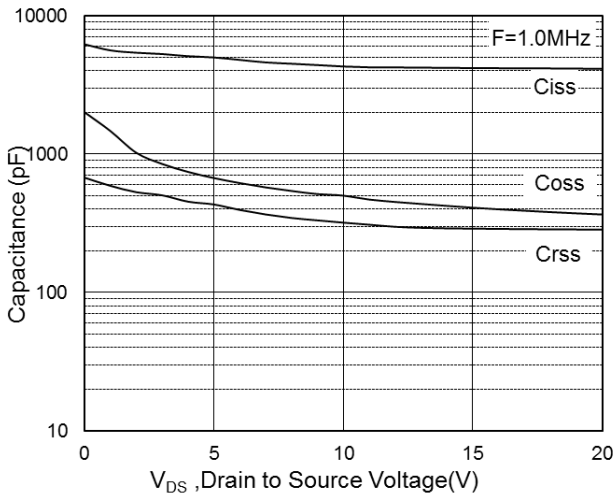


Fig.7 Capacitance

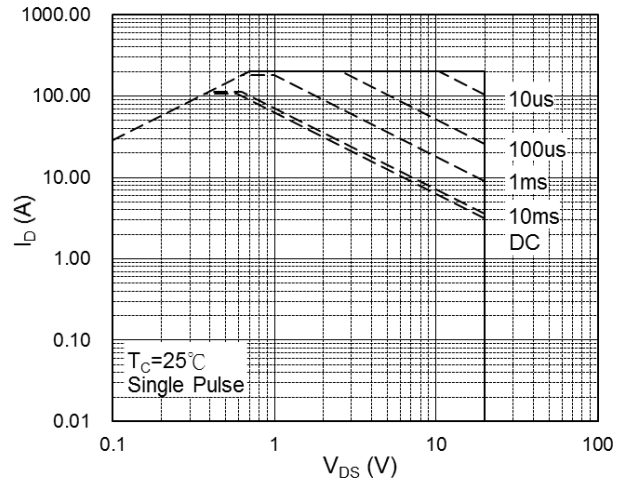


Fig.8 Safe Operating Area

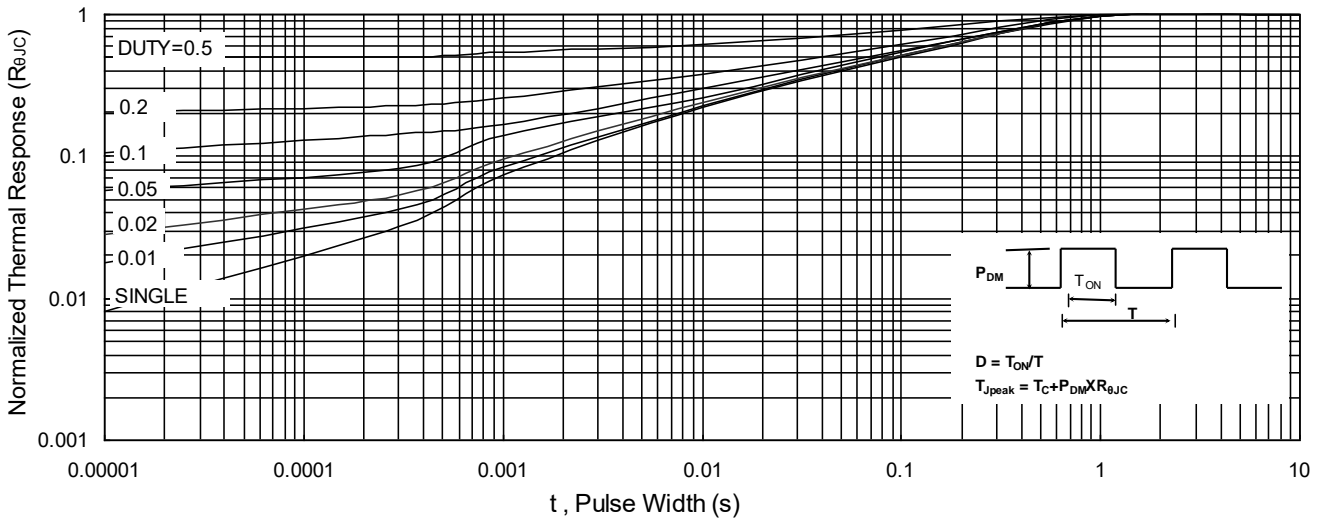


Fig.9 Normalized Maximum Transient Thermal Impedance

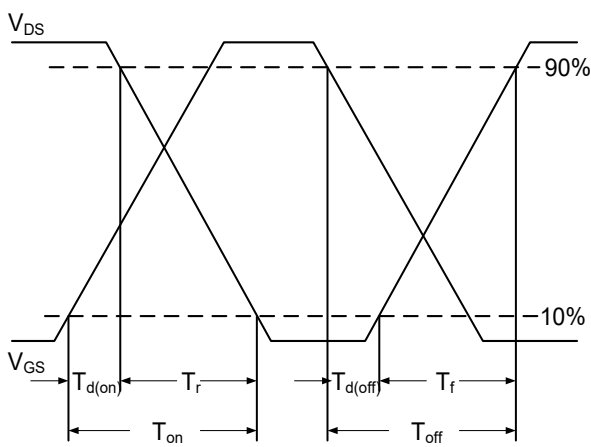


Fig.10 Switching Time Waveform

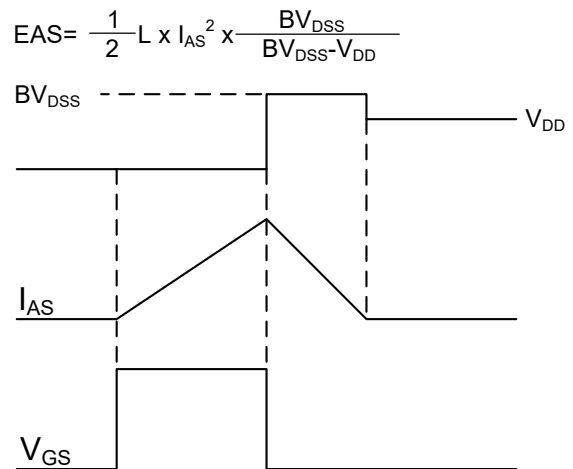
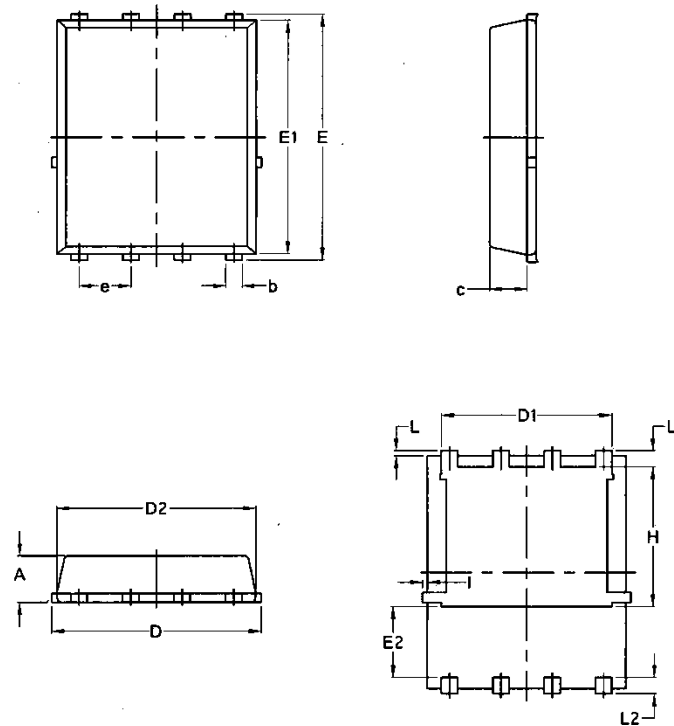


Fig.11 Unclamped Inductive Switching Waveform

Package Mechanical Data-DFN5*6-8L-JQ Single


| Symbol | Common | | | |
|--------|----------|--------|----------|--------|
| | mm | | Inch | |
| | Min | Max | Min | Max |
| A | 1.03 | 1.17 | 0.0406 | 0.0461 |
| b | 0.34 | 0.48 | 0.0134 | 0.0189 |
| c | 0.824 | 0.0970 | 0.0324 | 0.082 |
| D | 4.80 | 5.40 | 0.1890 | 0.2126 |
| D1 | 4.11 | 4.31 | 0.1618 | 0.1697 |
| D2 | 4.80 | 5.00 | 0.1890 | 0.1969 |
| E | 5.95 | 6.15 | 0.2343 | 0.2421 |
| E1 | 5.65 | 5.85 | 0.2224 | 0.2303 |
| E2 | 1.60 | / | 0.0630 | / |
| e | 1.27 BSC | | 0.05 BSC | |
| L | 0.05 | 0.25 | 0.0020 | 0.0098 |
| L1 | 0.38 | 0.50 | 0.0150 | 0.0197 |
| L2 | 0.38 | 0.50 | 0.0150 | 0.0197 |
| H | 3.30 | 3.50 | 0.1299 | 0.1378 |
| I | / | 0.18 | / | 0.0070 |

Flow (wave) soldering (solder dipping)

| Product | Peak Temperature | Dipping Time |
|----------------|------------------|--------------|
| Pb device | 245°C ±5°C | 5sec ±1 sec |
| Pb-Free device | 260°C +0/-5°C | 5sec ±1 sec |



This integrated circuit can be damaged by ESD. UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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